

2019 IEEE 7th Workshop on Wide Bandgap Power Devices and Applications (WiPDA 2019)

Raleigh, North Carolina, USA
29 – 31 October 2019



IEEE Catalog Number: CFP19WBP-POD
ISBN: 978-1-7281-3762-9

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IEEE Catalog Number:	CFP19WBP-POD
ISBN (Print-On-Demand):	978-1-7281-3762-9
ISBN (Online):	978-1-7281-3761-2

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